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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100vet6btr

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F100xC, STM32F100xD and STM32F100xE value line microcontrollers. In the rest of the document, the STM32F100xC, STM32F100xD and STM32F100xE are referred to as high-density value line devices.

This STM32F100xC, STM32F100xD and STM32F100xE datasheet should be read in conjunction with the STM32F100xx high-density ARM®-based 32-bit MCUs *reference manual (RM0059)*. For information on programming, erasing and protection of the internal Flash memory please refer to the *STM32F100xx high-density value line Flash programming manual (PM0072).* The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com.*

For information on the Cortex®-M3 core please refer to the Cortex®-M3 Technical Reference Manual, available from the http://infocenter.arm.com.

Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated for OS, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.2.18 I²C bus

The I²C bus interface can operate in multimaster and slave modes. It can support standard and fast modes.

It supports dual slave addressing (7-bit only) and both 7/10-bit addressing in master mode. A hardware CRC generation/verification is embedded.
The interface can be served by DMA and it supports SM Bus 2.0/PM Bus.

2.2.19 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32F100xx value line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3).

The available USART interfaces communicate at up to 3 Mbit/s. They provide hardware management of the CTS and RTS signals, they support IrDA SIR ENDEC, the multiprocessor communication mode, the single-wire half-duplex communication mode and have LIN Master/Slave capability.

The USART interfaces can be served by the DMA controller.

2.2.20 Universal asynchronous receiver transmitter (UART)

The STM32F100xx value line embeds 2 universal asynchronous receiver transmitters (UART4, and UART5).

The available UART interfaces support IrDA SIR ENDEC, the multiprocessor communication mode, the single-wire half-duplex communication mode and have LIN Master/Slave capability.

The UART interfaces can be served by the DMA controller.

2.2.21 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate up to 12 Mbit/s in slave and master modes in full-duplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits.

The SPIs can be served by the DMA controller.

Table 4. High-density STM32F100xx pin definitions (continued)

Pins			Pin name	Type[1]	I/O Level[2]	Main function[3] (after reset)	Alternate functions[4]	
LQFP144	LQFP100	LQFP64					Default	Remap
40	29	20	PA4	I/O	-	PA4	SPI1_NSS[8]/ USART2_CK[8] DAC_OUT1/ADC_IN4	-
41	30	21	PA5	I/O	-	PA5	SPI1_SCK[8] DAC_OUT2/ADC_IN5	-
42	31	22	PA6	I/O	-	PA6	SPI1_MISO[8]/ ADC_IN6 / TIM3_CH1[8]	TIM1_BKIN / TIM16_CH1
43	32	23	PA7	I/O	-	PA7	SPI1_MOSI[8]/ ADC_IN7 / TIM3_CH2[8]	TIM1_CH1N/ TIM17_CH1
44	33	24	PC4	I/O	-	PC4	ADC_IN14 / TIM12_CH1	-
45	34	25	PC5	I/O	-	PC5	ADC_IN15 / TIM12_CH2	-
46	35	26	PB0	I/O	-	PB0	ADC_IN8/TIM3_CH3	TIM1_CH2N / TIM13_CH1
47	36	27	PB1	I/O	-	PB1	ADC_IN9/TIM3_CH4[8]	TIM1_CH3N / TIM14_CH1
48	37	28	PB2	I/O	FT	PB2/BOOT1	-	-
49	-	-	PF11	I/O	FT	PF11	-	-
50	-	-	PF12	I/O	FT	PF12	FSMC_A6	-
51	-	-	V_{SS_6}	S	-	V_{SS_6}	-	-
52	-	-	V_{DD_6}	S	-	V_{DD_6}	-	-
53	-	-	PF13	I/O	FT	PF13	FSMC_A7	-
54	-	-	PF14	I/O	FT	PF14	FSMC_A8	-
55	-	-	PF15	I/O	FT	PF15	FSMC_A9	-
56	-	-	PG0	I/O	FT	PG0	FSMC_A10	-
57	-	-	PG1	I/O	FT	PG1	FSMC_A11	-
58	38	-	PE7	I/O	FT	PE7	FSMC_D4	TIM1_ETR
59	39	-	PE8	I/O	FT	PE8	FSMC_D5	TIM1_CH1N
60	40	-	PE9	I/O	FT	PE9	FSMC_D6	TIM1_CH1
61	-	-	V_{SS_7}	S	-	V_{SS_7}	-	-
62	-	-	V_{DD_7}	S	-	V_{DD_7}	-	-
63	41	-	PE10	I/O	FT	PE10	FSMC_D7	TIM1_CH2N
64	42	-	PE11	I/O	FT	PE11	FSMC_D8	TIM1_CH2
65	43	-	PE12	I/O	FT	PE12	FSMC_D9	TIM1_CH3N

Table 5. FSMC pin definition (continued)

Pins	FSMC		LQFP100(1)
	NOR/PSRAM/SRAM	NOR/PSRAM Mux	
PG0	A10	-	-
PG1	A11	-	-
PE7	D4	DA4	Yes
PE8	D5	DA5	Yes
PE9	D6	DA6	Yes
PE10	D7	DA7	Yes
PE11	D8	DA8	Yes
PE12	D9	DA9	Yes
PE13	D10	DA10	Yes
PE14	D11	DA11	Yes
PE15	D12	DA12	Yes
PD8	D13	DA13	Yes
PD9	D14	DA14	Yes
PD10	D15	DA15	Yes
PD11	A16	A16	Yes
PD12	A17	A17	Yes
PD13	A18	A18	Yes
PD14	D0	DA0	Yes
PD15	D1	DA1	Yes
PG2	A12	-	-
PG3	A13	-	-
PG4	A14	-	-
PG5	A15	-	-
PG6	-	-	-
PG7	-	-	-
PD0	D2	DA2	Yes
PD1	D3	DA3	Yes
PD3	CLK	CLK	Yes
PD4	NOE	NOE	Yes
PD5	NWE	NWE	Yes
PD6	NWAIT	NWAIT	Yes
PD7	NE1	NE1	Yes
PG9	NE2	NE2	-

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 19*. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- ambient operating temperature and V_{DD} supply voltage conditions summarized in *Table 6*.

Table 19. Peripheral current consumption

Peripheral		Typical consumption at 25 °C	Unit
AHB (up to 24MHz)	DMA1	12.50	µA/MHz
	DMA2	8.33	
	FSMC	28.33	
	CRC	1.25	
	BusMatrix[(1)]	16.67	

Table 19. Peripheral current consumption (continued)

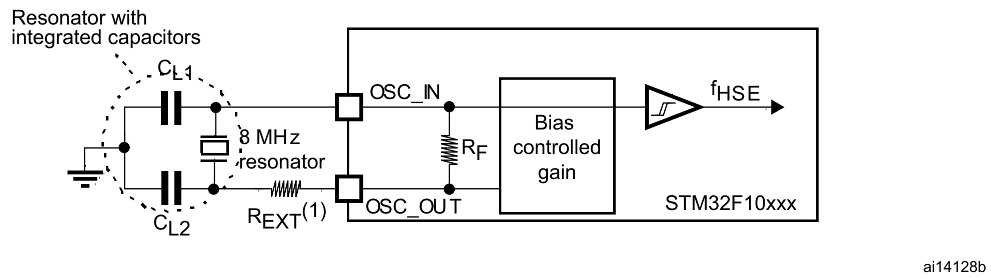
Peripheral		Typical consumption at 25 °C	Unit
APB1 (up to 24 MHz)	**APB1-Bridge**	3.75	µA/MHz
	TIM2	17.08	
	TIM3	17.50	
	TIM4	17.08	
	TIM5	17.08	
	TIM6	4.58	
	TIM7	4.17	
	TIM12	10.42	
	TIM13	7.08	
	TIM14	7.08	
	SPI2/I2S2	4.58	
	SPI3/I2S3	4.58	
	USART2	12.08	
	USART3	12.08	
	UART4	11.25	
	UART5	10.83	
	I2C1	10.42	
	I2C2	10.42	
	CEC	5.42	
	DAC(2)	7.92	
	WWDG	2.92	
	PWR	1.25	
	BKP	2.08	
	IWDG	3.33	

Table 22. HSE 4-24 MHz oscillator characteristics[1][2]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{L1} C_{L2}[3]	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)[4]	R_S = 30 Ω	-	30	-	pF
i_2	HSE driving current	V_{DD} = 3.3 V V_{IN} = V_{SS} with 30 pF load	-	-	1	mA
g_m	Oscillator transconductance	Startup	25	-	-	mA/V
$t_{SU(HSE)}$[5]	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization, not tested in production.
3. It is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.
4. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
5. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

Figure 13. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 23*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Note: For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and $C_{L2,}$ are usually the same size. The crystal manufacturer typically specifies a load capacitance which

is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.
For further details, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

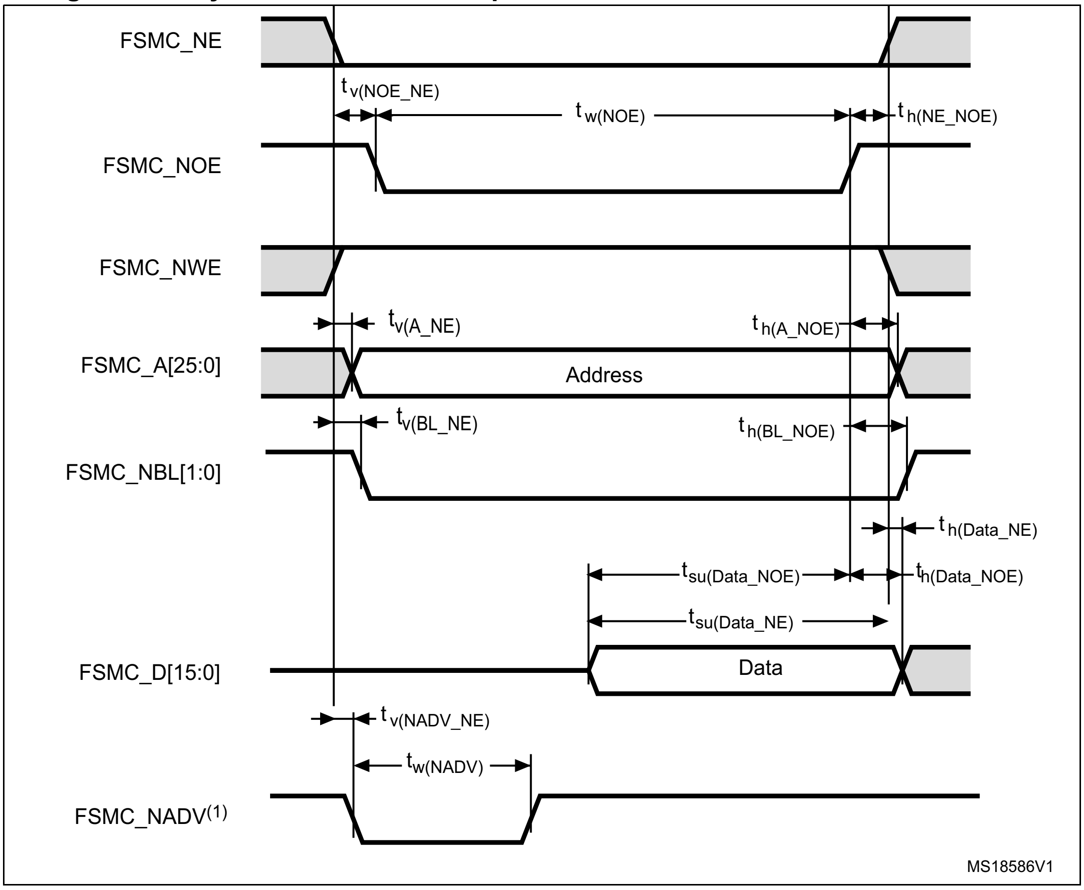
Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF, and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Table 23. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_F	Feedback resistor	-		-	5	-	MΩ
C_{L1} C_{L2}(2)	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 KΩ		-	-	15	pF
I_2	LSE driving current	V_{DD} = 3.3 V $V_{IN} = V_{SS}$		-	-	1.4	µA
g_m	Oscillator transconductance	-		5	-	-	µA/V
$t_{SU(LSE)}$(4)	Startup time	V_{DD} is stabilized	T_A = 50 °C	-	1.5	-	s
			T_A = 25 °C	-	2.5	-	
			T_A = 10 °C	-	4	-	
			T_A = 0 °C	-	6	-	
			T_A = -10 °C	-	10	-	
			T_A = -20 °C	-	17	-	
			T_A = -30 °C	-	32	-	
			T_A = -40 °C	-	60	-	

1. Based on characterization, not tested in production.
2. Refer to the note and caution paragraphs above the table.
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768 kHz. Refer to crystal manufacturer for more details
4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Figure 15. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms



1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Figure 18. Asynchronous multiplexed PSRAM/NOR write waveforms

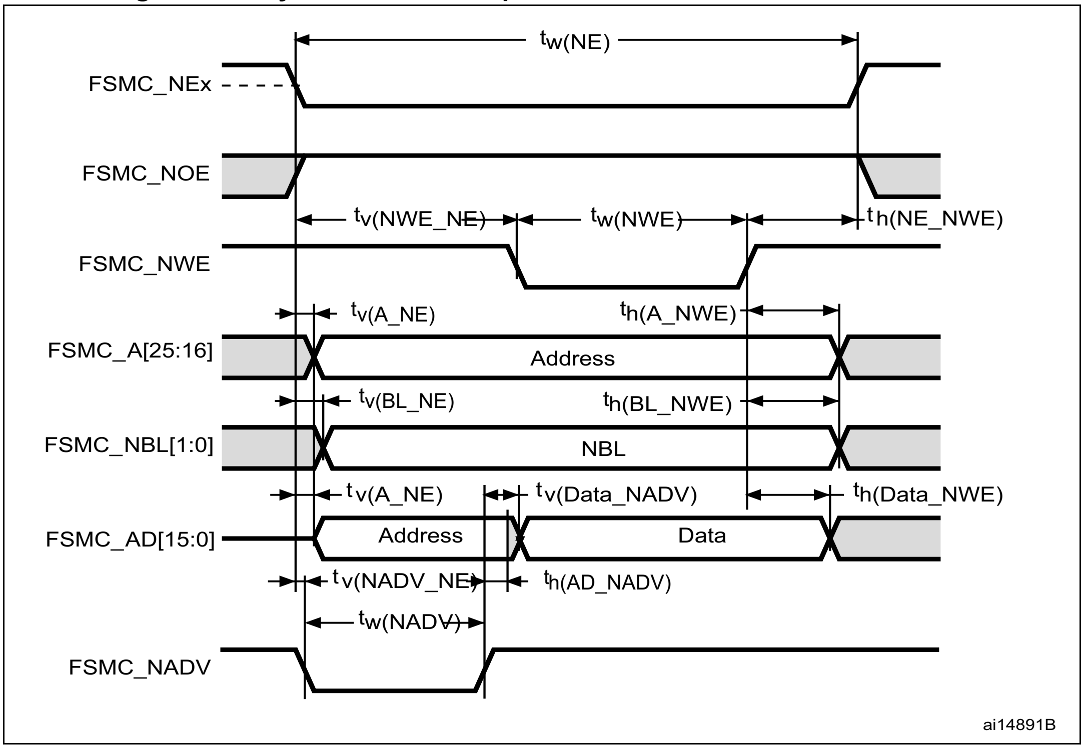


Table 33. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$5T_{HCLK} - 1$	$5T_{HCLK} + 2$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$2T_{HCLK}$	$2T_{HCLK} + 1$	ns
$t_{w(NWE)}$	FSMC_NWE low time	$2T_{HCLK} - 1$	$2T_{HCLK} + 2$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	$T_{HCLK} - 1$	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	7	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	3	5	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK} - 1$	$T_{HCLK} + 1$	ns
$t_{h(AD\_NADV)}$	FSMC_AD (address) valid hold time after FSMC_NADV high	$T_{HCLK} - 3$	-	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	$4T_{HCLK}$	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	1.6	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$T_{HCLK} - 1.5$	-	ns
$t_{v(Data\_NADV)}$	FSMC_NADV high to Data valid	-	$T_{HCLK} + 1.5$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	$T_{HCLK} - 5$	-	ns

1. C_L = 15 pF.
2. Preliminary values.

5.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (Electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 38*. They are based on the EMS levels and classes defined in application note AN1709.

Table 38. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 24 MHz, LQFP144 package, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 24 MHz, LQFP144 package, conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and pre qualification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second. To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

5.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in *Table 42*

Table 42. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13	-0	+0	mA
	Injected current on all FT pins	-5	+0	
	Injected current on any other pin	-5	+5	

Figure 23. Standard I/O input characteristics - CMOS port

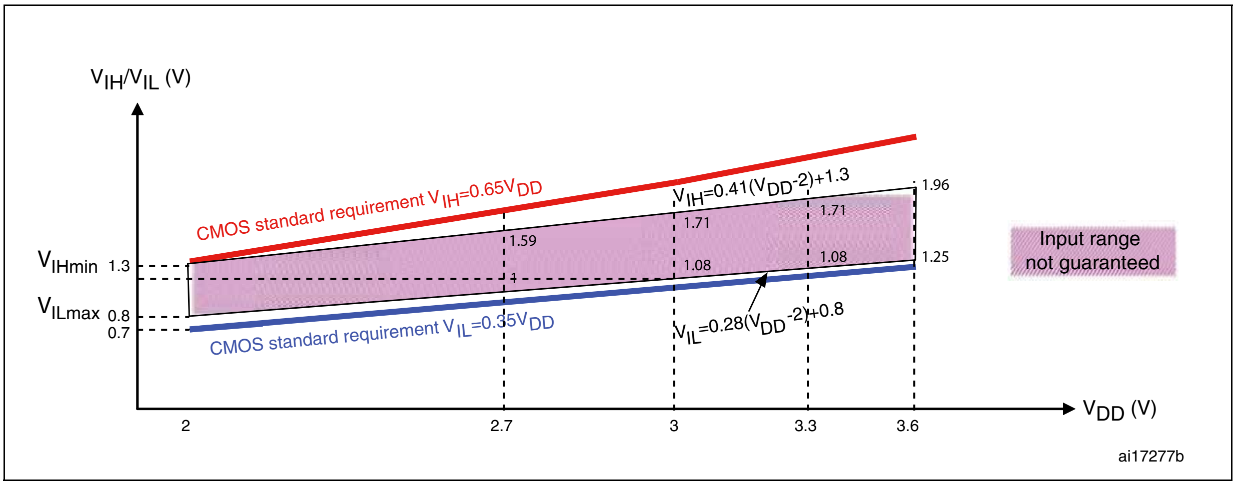
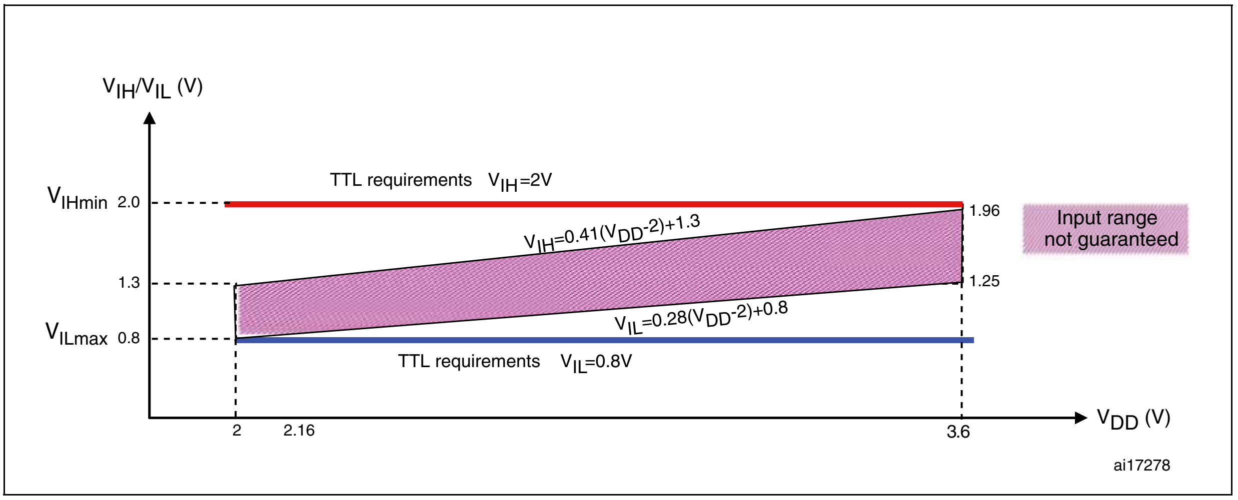


Figure 24. Standard I/O input characteristics - TTL port



Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 27* and *Table 45*, respectively.

Unless otherwise specified, the parameters given in *Table 45* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 45. I/O AC characteristics[1]

MODEx [1:0] bit value[1]	Symbol	Parameter	Conditions	Max	Unit
10	$f_{max(IO)out}$	Maximum frequency[2]	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	2[3]	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	125[3]	ns
	$t_{r(IO)out}$	Output low to high level rise time		125[3]	
01	$f_{max(IO)out}$	Maximum frequency[2]	C_L= 50 pF, V_{DD} = 2 V to 3.6 V	10[3]	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L= 50 pF, V_{DD} = 2 V to 3.6 V	25[3]	ns
	$t_{r(IO)out}$	Output low to high level rise time		25[3]	
11	$f_{max(IO)out}$	Maximum frequency[2]	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	24	MHz
	$t_{f(IO)out}$	Output high to low level fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	5[3]	ns
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	8[3]	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	12[3]	
	$t_{r(IO)out}$	Output low to high level rise time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	5[3]	
			C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	8[3]	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	12[3]	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10[3]	ns

1. The I/O speed is configured using the MODEx[1:0] bits. Refer to the STM32F100xx reference manual for a description of GPIO Port configuration register.
2. The maximum frequency is defined in *Figure 27*.
3. Guaranteed by design, not tested in production.

SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 50* are preliminary values derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 9*.

Refer to *Section 5.3.13: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 50. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	12	MHz
		Slave mode	-	12	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$ (1)	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}$ (1)	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}$ (1) $t_{w(SCKL)}$ (1)	SCK high and low time	Master mode, f_{PCLK} = 24 MHz, presc = 4	50	60	
$t_{su(MI)}$ (1) $t_{su(SI)}$ (1)	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}$ (1)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$ (1)		Slave mode	4	-	
$t_{a(SO)}$ (1)(2)	Data output access time	Slave mode, f_{PCLK} = 24 MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}$ (1)(3)	Data output disable time	Slave mode	2	10	
$t_{v(SO)}$ (1)	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}$ (1)	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}$ (1)	Data output hold time	Slave mode (after enable edge)	15	-	
$t_{h(MO)}$ (1)		Master mode (after enable edge)	2	-	

1. Preliminary values.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Table 51. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V_{REF+}	Positive reference voltage	-	2.4	-	V_{DDA}	V
I_{VREF}	Current on the V_{REF} input pin	-	-	160(1)	220(1)	µA
f_{ADC}	ADC clock frequency	-	0.6	-	12	MHz
f_S(2)	Sampling rate	-	0.05	-	1	MHz
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 12 MHz	-	-	823	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}(3)	Conversion voltage range	-	0 (V_{SSA} tied to ground)	-	V_{REF+}	V
R_{AIN}(2)	External input impedance	See *Equation 1* and *Table 52* for details	-	-	50	kΩ
R_{ADC}(2)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(2)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL}(2)	Calibration time	f_{ADC} = 12 MHz	5.9			µs
		-	83			$1/f_{ADC}$
t_{lat}(2)	Injection trigger conversion latency	f_{ADC} = 12 MHz	-	-	0.214	µs
		-	-	-	3(4)	$1/f_{ADC}$
t_{latr}(2)	Regular trigger conversion latency	f_{ADC} = 12 MHz	-	-	0.143	µs
		-	-	-	2(4)	$1/f_{ADC}$
t_S(2)	Sampling time	f_{ADC} = 12 MHz	0.125	-	17.1	µs
			1.5	-	239.5	$1/f_{ADC}$
t_{STAB}(2)	Power-up time	-	0	0	1	µs
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 12 MHz	1.17	-	21	µs
		-	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. Preliminary values.
2. Guaranteed by design, not tested in production.
3. V_{REF+} is internally connected to V_{DDA}
4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 51*.

Equation 1: R_{AIN} max formula:

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The above formula (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

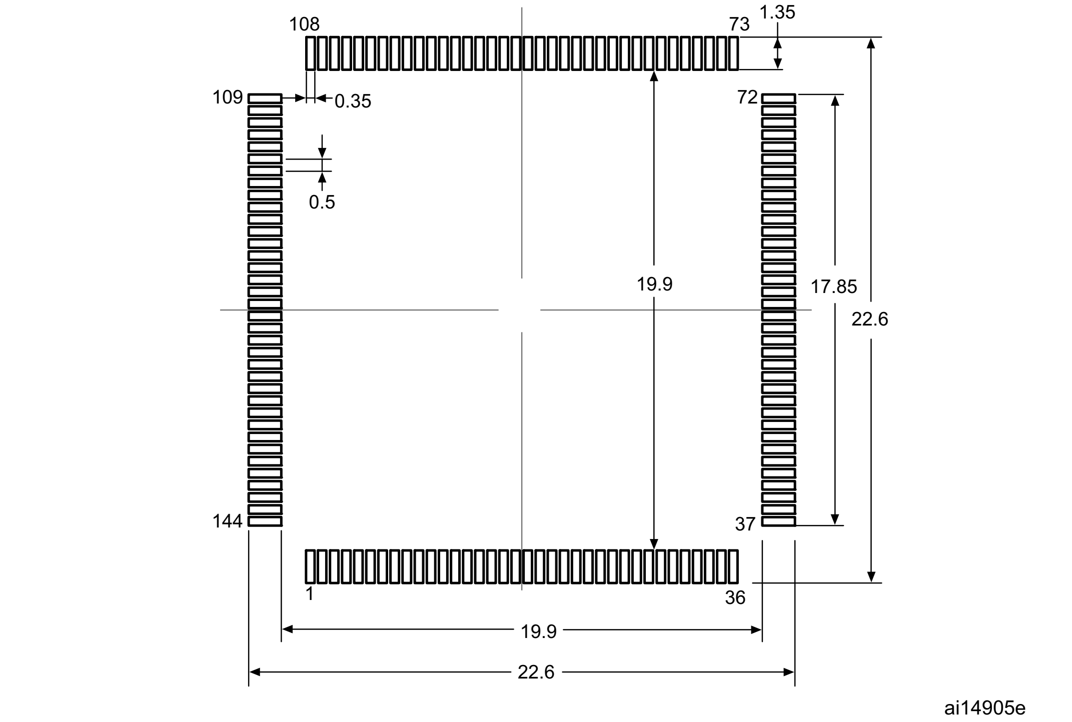
5.3.20 Temperature sensor characteristics

Table 56. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{25}(1)	Voltage at 25°C	1.32	1.41	1.50	V
t_{START}(2)	Startup time	4	-	10	µs
T_{S_temp}(3)(2)	ADC sampling time when reading the temperature	-	-	17.1	µs

1. Guaranteed by characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

Figure 39. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package recommended footprint

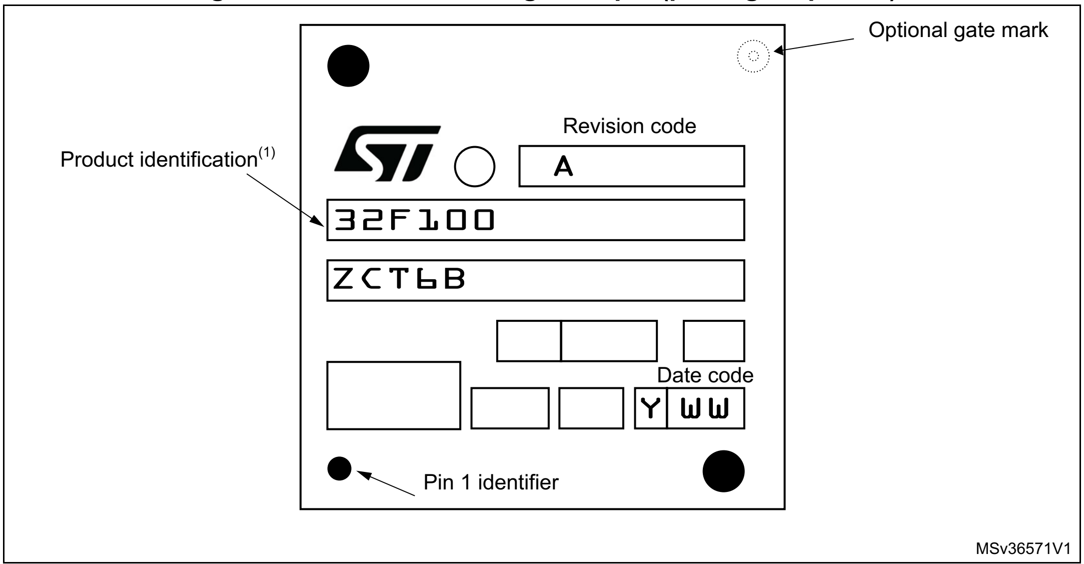


1. Dimensions are expressed in millimeters.

Device marking for LQFP144

The following figure shows the device marking for the LQFP144 package.

Figure 40.LQFP144 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.